

## ABSTRACT OF THE DISCLOSURE

The present invention provides a resist pattern thickening material and the like which can thicken a resist pattern and form a fine space pattern, exceeding exposure limits of exposure light used during patterning. The resist pattern thickening material contains a resin and a surfactant. In a process for forming a resist pattern of the present invention, after a resist pattern to be thickened is formed, the resist pattern thickening material is coated on a surface thereof. A process for manufacturing a semiconductor device of the present invention includes: a step of, after forming a resist pattern to be thickened on an underlying layer, coating the thickening material on a surface of the resist pattern to be thickened so as to thicken the resist pattern to be thickened and form a resist pattern; and a step of patterning the underlying layer by etching by using the resist pattern.